

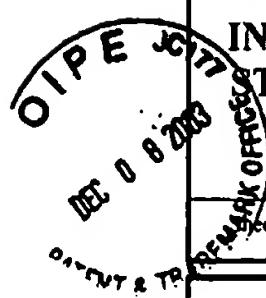
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet

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of

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Complete if Known

Application Number	09/832,867
Filing Date	April 12, 2001
First Named Inventor	Shunpei YAMAZAKI, et al.
Group Art Unit	2822
Examiner Name	Monica Lewis

Attorney Docket Number

0756-2294

U.S. PATENT DOCUMENTS

Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
SLC		4,963,504		Huang	10/16/90	
		5,323,042		Matsumoto	06/21/94	
		5,399,502		Friend et al.	03/21/95	
		5,412,240		Inoue et al.	05/02/95	
		5,532,175		Racanelli et al.	07/02/96	
		5,543,340		Lee	08/06/96	
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		5,583,067		Sanchez	12/10/96	
		5,581,092		Takemura	12/03/96	
		5,585,295		Wu	12/17/96	
		5,594,569		Konuma et al.	01/14/97	
		5,637,519		Tsai et al.	06/10/97	
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		5,757,444		Takemura	05/26/98	
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		5,923,961		Shibuya et al.	07/13/99	
		6,153,445		Yamazaki et al.	11/28/00	
		6,166,397		Yamazaki et al.	12/26/00	
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		6,198,133		Yamazaki et al.	03/06/01	
		6,211,536		Zhang	04/03/01	
		6,259,138		Ohtani et al.	07/10/01	
		6,274,400		Jen	08/14/01	
		6,274,887		Yamazaki et al.	08/14/01	
SLC		6,277,679		Ohtani	08/21/01	

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First Named Inventor	Shunpei YAMAZAKI, et al.
Group Art Unit	2822
Examiner Name	Monica Lewis
Attorney Docket Number	0756-2294

Sheet

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U.S. PATENT DOCUMENTS

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		Number	Kind Code ² (if known)			
<i>SLC</i>		6,281,552		Kawasaki et al.	08/28/01	
<i>SLC</i>		6,284,577		Suzawa et al.	09/04/01	
<i>SLC</i>		6,303,963		Ohtani et al.	10/16/01	
<i>SLC</i>		6,306,694		Yamazaki et al.	10/23/01	
<i>SLC</i>		6,337,731		Takemura	01/08/02	
<i>SLC</i>		6,346,730		Kitakado et al.	02/12/02	
<i>SLC</i>		6,358,766		Kasahara	03/19/02	
<i>SLC</i>		6,362,507		Ogawa et al.	03/26/02	
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<i>SLC</i>		6,384,808		Azami	05/07/02	
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<i>SLC</i>		6,469,317		Yamazaki et al.	10/22/02	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ³
<i>SLC</i>		US Patent Application Serial No. 10/386,257 including specification, drawings, claims, and filing receipt; filed March 11, 2003; Inventor: Hideto Ohnuma.	
<i>SLC</i>		US Patent Application Serial No. 09/454,146 including specification, drawings, claims, and filing receipt; filed December 3, 1999; Inventors: Shunpei YAMAZAKI, et al.	
<i>SLC</i>		Yoshida et al., "A Full-Color Thresholdless Antiferroelectric LCD Exhibiting Wide Viewing Angle with Fast Response Time," SID 97 DIGEST, pp. 841-844.	ENG
<i>SLC</i>		Hwang et al., "High Performance Submicron SOI/CMOS with an Elevated Source/Drain Structure," PROCEEDINGS OF THE ANNUAL SOS/SOI TECHNOLOGY CONFERENCE, IEEE, Vol. 19, 1993, pp. 132-133.	ENG
<i>SLC</i>		Choi et al., "Gate-Overlapped Lightly Doped Drain Poly-Si Thin-Film Transistors for Large Area-AMLCD," IEEE TRANSACTIONS ON ELECTRON DEVICES, Vol. 45, No. 6, June, 1998, pp. 1272-1279.	ENG

Examiner Signature	<i>[Signature]</i>	Date Considered	4/4/04
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Attorney Docket Number	0756-2294		

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FOREIGN PATENT DOCUMENTS

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		Office ³	Number ⁴	Kind Code ⁵ (if known)			
<i>SLC</i>	JP	04-369271		Takeda et al.	12/22/92		FULL
	JP	05-102483		Ueda	04/23/93		FULL
	JP	06-037314		Tsuchimoto	02/10/94		AB
	JP	07-202210		Taniguchi	08/04/95		AB
	JP	08-078329		Otani	03/22/96		AB
	JP	08-051207		Sato	02/20/96		AB
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	JP	10-135469		Yamazaki et al.	05/22/98		AB
	JP	10-144929		Shibuya et al.	05/29/98		AB
	EP	0 451 968		Coxon	10/16/91		ENG
	JP	10-247735		Takano et al.	09/14/98		AB
	EP	0 803 911		Adan et al.	10/29/97		ENG
<i>SLC</i>	JP	10-135468		Yamazaki et al.	05/22/98		AB

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

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<i>SLC</i>		Tanaka, et al., "Ultrafast Operation of V _{th} -Adjusted p ⁺ -n ⁺ Double-Gate SOI MOSFET'S," IEEE Electron Device Letters, Vol. 15 (Oct., 1994), No. 10, pp. 386-388.	ENG
		Inui et al., "Thresholdless Antiferroelectricity in Liquid Crystals and its Application to Displays," J. Mater Chem., 1996, 6(4), pp. 671-673.	ENG
		Takada, et al., PROCEEDINGS OF 46 TH SPRING MEETINGS OF THE SOCIETY FOR APPLIED PHYSICS OF JAPAN, 28P-V-8, page 1316.	NONE
		Hwang et al., "Novel Polysilicon/TiN Stacked-Gate Structure for Fully-Depleted SOI/CMOS," IEDM '92, pp. 345-348.	ENG
		Yoshihara, EKISHO, Vol. 3, No. 3, pp. 190-194.	NONE
		Furue et al., "P-78: Characteristics and Driving Scheme of Polymer-Stabilized Monostable FLCD Exhibiting Fast Response Time and High Contrast Ratio with Gray-Scale Capability," SID '98 DIGEST, pp. 782-785.	ENG
<i>SLC</i>		Hatano et al., "A Novel Self-Aligned Gate-Overlapped LDD Poly-Si TFT with High Reliability and Performance," IEDM '97, pp. 523-526.	ENG

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